

Amendments to the Claims:

Please cancel claims 78 and 79 and 81-94, and amend claim 73 as follows:

Listing of Claims:

1-72. (Cancelled)

1
~~73.~~ (Currently Amended) An in-process device, comprising:

a substrate; [[and]]

E1
a conductive layer comprising a metal layer over the substrate, the conductive layer being exposed to a material selected from the group consisting of phosphine and methylsilane to reduce an ability of the conductive layer to associate with oxygen[.]; and
a second conductive layer comprising a tungsten nitride layer formed on the conductive layer and a third conductive layer comprising a copper layer formed on the second conductive layer.

2
~~74.~~ (Previously Presented) The in-process device of claim ~~73~~, wherein the conductive layer comprises tungsten nitride.

3
~~75.~~ (Previously Presented) The device in claim ~~74~~, further comprising another conductive layer formed on the tungsten nitride layer.

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76. (Cancelled)

4
~~77.~~ (Previously Presented) The in-process device of claim ~~75~~ wherein the other conductive layer comprises copper.

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78-79. (Cancelled)

5 80 (Previously Presented) The in-process device of claim ¹~~73~~ wherein the substrate comprises a silicon substrate.

61 [81-94 (Cancelled)
